

forming a polyimide film, which serves [is served] as a buffer coating film, on the passivation film;

patterning the polyimide film;

etching the passivation film, while the patterned polyimide film is used [taken] as a mask, under conditions which form a hardened polyimide layer on the surface of the polyimide film;

[removing, through] ashing to remove 0.1 to several micrometers of the polyimide film, thereby removing the [process, a] hardened layer formed on the surface of the polyimide film as a result of said step of etching; and

curing the semiconductor substrate after ashing process so as to transform the polyimide film into imide.

Please cancel claim 5.

REMARKS

Claim 1 through 4 and 6 are pending in this Application. Claim 1 ahs been amended and claim 5 cancelled. Care has been exercised to avoid the introduction of new matter. Indeed, the limitations of claim 5 have been incorporated into claim 1, and claim 1 clarified by reciting that the passivation film is etched under conditions to form a hardened layer on the surface of the polyimide film, adequate descriptive support for which should be apparent throughout the originally filed disclosure as, for example, the paragraph bridging pages 5 and 6 of the written description of the specification.

Applicants submit that the present Amendment does not generate any new matter issue.